

isc Silicon NPN Power Transistors

2SD1062

DESCRIPTION

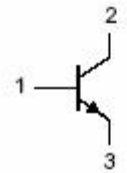
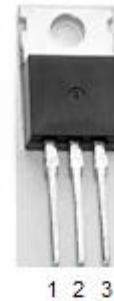
- Low Collector Saturation Voltage
: $V_{CE(sat)} = 0.4V(\text{Max}) @ I_C = 6A$
- Wide Area of Safe Operation
- Complement to Type 2SB826
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

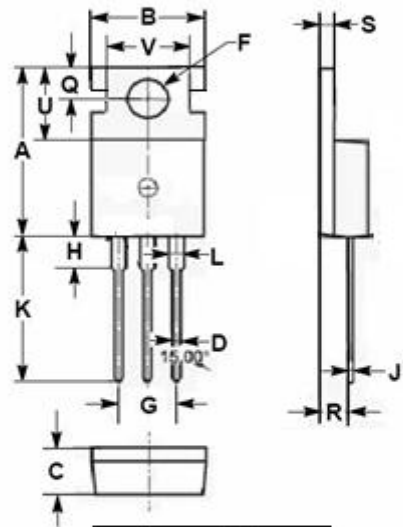
- Designed for relay drivers, high-speed inverters, converters, and other general high-current switching applications

ABSOLUTE MAXIMUM RATINGS($T_a = 25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	60	V
V_{CEO}	Collector-Emitter Voltage	50	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current-Continuous	12	A
I_{CP}	Collector Current-Pulse	15	A
P_C	Collector Power Dissipation @ $T_C = 25^\circ\text{C}$	40	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55~150	$^\circ\text{C}$



PIN 1. BASE
2. COLLECTOR
3. EMITTER
TO-220C package



DIM	mm	
	MIN	MAX
A	15.50	15.90
B	9.80	10.20
C	4.20	4.50
D	0.70	0.90
F	3.40	3.70
G	4.98	5.18
H	2.68	2.90
J	0.44	0.60
K	12.80	13.40
L	1.20	1.45
Q	2.70	2.90
R	2.30	2.70
S	1.29	1.35
U	6.45	6.65
V	8.66	8.86

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ELECTRICAL CHARACTERISTICS

T_c=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = 1mA ; R _{BE} = ∞	50			V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	I _C = 1mA ; I _E = 0	60			V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	I _E = 1mA ; I _C = 0	6			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 6A; I _B = 0.3A			0.4	V
I _{CBO}	Collector Cutoff Current	V _{CB} = 40V; I _E = 0			100	μ A
I _{EBO}	Emitter Cutoff Current	V _{EB} = 4V; I _C =0			100	μ A
h _{FE-1}	DC Current Gain	I _C = 1A ; V _{CE} = 2V	70		280	
h _{FE-2}	DC Current Gain	I _C = 5A ; V _{CE} = 2V	30			
f _T	Current-Gain—Bandwidth Product	I _C = 1A ; V _{CE} = 5V		10		MHz

Switching times

t _{on}	Turn-on Time	I _C = 5A; I _{B1} = -I _{B2} = 0.5A R _L = 4 Ω ; P _W =20 μ s		0.1		μ s
t _{stg}	Storage Time			1.2		μ s
t _f	Fall Time			0.05		μ s

◆ h_{FE-1} Classifications

Q	R	S
70-140	100-200	140-280

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